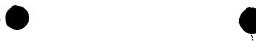




L	Hits	Search Text	DB	Time stamp
Number 1	0	438/257,263, 264,762,763.ccls. and	USPAT;	2004/04/17
2	588	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) 438/257,263,264,762,763.ccls. and (memory	US-PGPUB; EPO; JPO; DERWENT USPAT;	14:34 2004/04/17
2	366	adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate)	US-PGPUB; EPO; JPO; DERWENT	14:34
3		438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 14:36
4	3	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:15
5		6136652.pn. and (oxide same "40")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:12
6	1	6136652.pn. and (oxide same "40" adj angstroms)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:12
7	0	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and ((p adj channel) or p-channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:16
8		438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:17
9		438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and (erase same volt\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17
10	1	6136652.pn. and (erase same volt\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:23
11	1	6136652.pn. and (erase same volt\$3 same (floating adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:30
12		6245613.pn. and (erase same volt\$3 same (floating adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:30
13	0	6246089.pn. and (erase same volt\$3 same (floating adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:31
-	790596	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/26 14:01
-	1819	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 14:38



-	. 53	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj	USPAT; US-PGPUB; EPO; JPO;	2003/07/11 19:01
_ .	791060	layer with "50" adj angstroms memory adj cell and oxide adj layer and	DERWENT USPAT;	2003/07/10
		floating adj gate and dielectric adj layer and control gate	US-PGPUB; EPO; JPO; DERWENT	17:10
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	2003/07/11 19:02
	:	layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 adj micron adj gate	EPO; JPO; DERWENT	
-	. 43	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	2003/11/13 11:11
		layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or quarter adj micron adj gate	EPO; JPO; DERWENT	
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	2003/07/11 19:04
		layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.25 or quarter) adj micron	EPO; JPO; DERWENT	
-	15	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.25 or	USPAT; US-PGPUB; EPO; JPO;	2003/07/12 11:35
_	0	quarter) adj micron (memory adj cell and oxide adj layer and	DERWENT USPAT;	2003/07/11
		floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.25 or	US-PGPUB;" EPO; JPO; DERWENT	19:28
_	0	quarter) adj micron (memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	2003/07/12 11:32
		layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.18 or	EPO; JPO; DERWENT	11.32
-	. 0	quarter) adj micron (memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	2003/07/12 11:33
		layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.18)	EPO; JPO; DERWENT	
-	0	adj micron (memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	2003/07/12 11:33
	0	layer and control adj gate) and (.18) adj micron (memory adj cell and oxide adj layer and	EPO; JPO; DERWENT USPAT;	2003/07/12
		floating adj gate and dielectric adj layer and control adj gate) and (.15) adj	US-PGPUB; EPO; JPO;	11:33
-	0	micron (memory adj cell and oxide adj layer and floating adj gate and dielectric adj	DERWENT USPAT; US-PGPUB;	2003/07/12 11:33
	0	layer and control adj gate) and (.1) adj micron (.1) adj micron	EPO; JPO; DERWENT USPAT;	2003/07/12
	J	(.1) adj micion	US-PGPUB; EPO; JPO;	11:34
-	0	(.18) adj micron	DERWENT USPAT; US-PGPUB;	2003/07/12 11:34
	0	(.25) adj micron	EPO; JPO; DERWENT USPAT;	2003/07/12
	U	(.23) adj micron	US-PGPUB; EPO; JPO;	11:34
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj	DERWENT USPAT; US-PGPUB;	2003/07/12 11:35
		layer and control adj gate) and (.25) adj micron	EPO; JPO; DERWENT	



			<u>"</u>	
-	15	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:36
		layer and control adj gate) and (.25 or	EPO; JPO;	
		quarter) adj micron	DERWENT	
-	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:36
		layer and control adj gate) and (.25) adj	EPO; JPO;	
	4.5	micron	DERWENT	2002/07/12
_	43	438/257.CCLS. AND (memory adj cell and	USPAT;	2003/07/13 16:25
		oxide adj layer and floating adj gate and dielectric adj layer and control adj	US-PGPUB; EPO; JPO;	16:25
		gate) and oxide adj layer with "50" adj	DERWENT	
		angstroms and .25 or quarter adj micron	DEKWENT	İ
		adj gate		
_	43	257/315,316.CCLS. AND 438/257.CCLS. AND	USPAT;	2003/07/13
		(memory adj cell and oxide adj layer and	US-PGPUB;	16:26
		floating adj gate and dielectric adj	EPO; JPO;	
		layer and control adj gate) and oxide adj	DERWENT	
		layer with "50" adj angstroms and .25 or		
		quarter adj micron adj gate		
-	48	memory adj cell and oxide adj layer and	USPAT;	2003/11/13
		floating adj gate and dielectric adj	US-PGPUB;	12:16
		layer and control adj gate and oxide adj	EPO; JPO;	
1		layer with "50" adj angstroms and .25 or	DERWENT	
	1 - 2 -	quarter adj micron adj gate	IICDAM -	2002/11/12
1-	1797	memory adj cell and oxide adj layer and	USPAT;	2003/11/13
		floating adj gate and dielectric adj layer and control adj gate and oxide adj	US-PGPUB; EPO; JPO;	12:08
		layer and "50" adj angstroms and .25 or	DERWENT	
		quarter adj micron	DEKWENT	
<u>-</u>	l 0	(memory adj cell) and (oxide adj layer)	USPAT;	2003/11/13
	Ĭ	and (floating adj gate) and (dielectric	US-PGPUB;	12:22
		adj layer) and (control adj gate) and	EPO; JPO;	
		((oxide adj layer) with ("50" adj	DERWENT	
		angstroms) and (.25 or quarter adj micron		
		adj gate))		
-	57	(memory adj cell) and (oxide adj layer)	USPAT;	2003/11/13
		and (floating adj gate) and (dielectric	US-PGPUB;	18:04
		adj layer) and (control adj gate) and	EPO; JPO;	
		((oxide adj layer) with ("50" adj	DERWENT	
		angstroms))	TIGDEM.	2003/11/13
-	0	257/315,316.ccls and (memory adj cell) and (oxide adj layer) and (floating adj	USPAT; US-PGPUB;	16:38
		gate) and (dielectric adj layer) and	EPO; JPO;	10.50
		(control adj gate) and ((oxide adj layer)	DERWENT	
		with ("50" adj angstroms))		
-	9	438/264,762,763.ccls. and (memory adj	USPAT;	2003/11/13
1		cell) and (oxide adj layer) and (floating	US-PGPUB;	18:01
1		adj gate) and (dielectric adj layer) and	EPO; JPO;	
1		(control adj gate) and ((oxide adj layer)	DERWENT	
1		with ("50" adj angstroms))		
-	. 0	438/264,762,763.ccls. and (memory adj	USPAT;	2003/11/29
1		cell) and (oxide adj layer) and (floating	US-PGPUB;	16:04
		adj gate) and (dielectric adj layer) and	EPO; JPO;	
		<pre>(control adj gate) and ((oxide adj layer) with ("23" adj angstroms))</pre>	DERWENT	
_	o	With ("23" adj angstroms) 6515328.pn. and (p adj channel)	USPAT;	2003/11/13
		colored pit and the adj chaimely	US-PGPUB;	17:41
			EPO; JPO;	- · · · -
1			DERWENT	
-	0	6515328.pn. and (p adj channel or	USPAT;	2003/11/13
		positiv\$3 adj dop\$3)	US-PGPUB;	17:43
			EPO; JPO;	
	·		DERWENT	
-	0	6515328.pn. and ((p adj channel) or	USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:44
1			EPO; JPO;	
		E052211 nn and //n add abanally ar	DERWENT	2002/11/12
1 -	0	5852311.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; US-PGPUB;	2003/11/13 17:45
1		(hostcinss and dobss))	EPO; JPO;	11.40
1			DERWENT	
	L	<u> </u>	TOTAMETAT	



_			
-	0	5869370.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:46 EPO; JPO;
-	0	6515328.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	DERWENT USPAT; 2003/11/13 US-PGPUB; 17:46
_	. о	6383939.pn. and ((p adj channel) or	EPO; JPO; DERWENT USPAT; 2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB; 17:47 EPO; JPO; DERWENT USPAT; 2003/11/13
-	0	6316316.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:47 EPO; JPO; DERWENT
-	1	6456535.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:48 EPO; JPO; DERWENT
-	0	6261906.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:48 EPO; JPO;
_	0	6261906.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT
-	. 0	5852311.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:49 EPO; JPO; DERWENT
-	0	5869370.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:50 EPO; JPO; DERWENT
-	0	5852311.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:50 EPO; JPO; DERWENT
-		5869370.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:50 EPO; JPO; DERWENT
-	0	6515328.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:51 EPO; JPO; DERWENT
-	0	6316316.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:51 EPO; JPO; DERWENT
-	. 1	6456535.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:51 EPO; JPO; DERWENT
_	0	6261906.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; 2003/11/13 US-PGPUB; 17:55 EPO; JPO;
-	0	6372651.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; 2003/11/13 US-PGPUB; 17:56 EPO; JPO;
-	, 0	6383939.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; 2003/11/13 US-PGPUB; 17:56 EPO; JPO; POO; POO; POO; POO; POO; POO; P
-	0	6515328.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; 2003/11/13 US-PGPUB; 17:57 EPO; JPO;
		<u> </u>	DERWENT



(positiv3 same dop\$3)				· V 1'	
- 1 645555.pn. and ((p adj channel) or (positiv33 same dop53) - 0 6249819.pn. and ((p adj channel) or (positiv33 same dop53)) - 0 20030201477.pn. and ((p adj channel) or (positiv33 same dop53)) - 0 20030201477.pn. and ((p adj channel) or (positiv33 same dop53)) - 0 438/264,762,763.ccls. and (memory adj cell) and (coxide adj layer) and (floating adj channel) or (positiv51 same dop53) - 0 438/264,762,763.ccls. and (memory adj cell) and (coxide adj layer) and (floating adj channel) or (p-channel)) - 18 (memory adj cell) and (oxide adj layer) and (floating adj gate) and ((oxide adj layer) and (floating adj gate) and ((oxide adj layer) and (floating adj gate) and ((p-channel)) or (p-channel) or (p-cha	-	0	6316316.pn. and ((p adj channel) or	USPAT;	2003/11/13
1 6456335,pn. and ((p adj channel) or (positiv33 same dop\$3))			(positives same dopes)		17.37
			C45C525 and //n add abancal\ an		2002/11/12
- 0 6249819.pn. and ((p adj channel) or (positiv33 same dop\$31)	-	1		·	
0			(Personal State of Party of Pa	EPO; JPO;	
(positiv\$3 same dop\$3)		١ ,	6240010 pp and //p add channell or		2002/11/12
- 0 20030201477.pn. and ((p adj channel) or (positiv\$3 same dop\$3)) - 0 438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (control adj gate) and (coxide adj layer) and (control adj gate) and (coxide adj layer) and (control adj gate) and (coxide adj layer) and (floating adj gate) and (coxide adj layer) and (floating adj gate) and (coxide adj layer) and (floating adj gate) and ((p-channel) or (p adj channel)) - 303 (memory adj cell) and (oxide adj layer) and (floating adj gate) and (coxide adj layer) and (floating adj gate) and (coxide adj layer) and (coxide adj	-	ľ			
- 0 20030201477.pn. and ([p adj channel) or (positiv\$3 same dop\$3)) - 0 4387264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (coxide adj layer) and (control adj gate) and (coxide adj layer) and (floating adj gate) and (coxide adj layer) and (floating adj gate) and (floating			• • • • • • • • • • • • • • • • • • • •		
(positiv\$3 same dop\$3) US-PGPUB; EPO; JPO; DERWENT cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (control adj gate) and (control adj gate) and (control adj layer) and (floating adj gate) and (dielectric adj layer) and (floating adj gate) and (dielectric adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (control adj adj angstroms)) and ((p-channel) or (p adj channel)) - 13 (memory adj cell) and (oxide adj layer) and (control adj gate) and (dielectric adj layer) and (potentanel) or (p adj channel)) - 13 (memory adj cell) and (oxide adj layer) under (coxide adj layer) with ("30" adj angstroms)) and (potentanel) or (p adj channel) or (p adj channel)) - 200 (6372651.pn. and (potentanel or p adj channel) or (padj ch	_	0	20030201477 pp and (/p adi channel) or		2003/11/13
- 0 438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (floating adj gate) and (control adj gate) and (coxide adj layer) with ("50" adj angstroms)) and ((padj channel) or (p-channel) and (p-channel) or (padj channel) and ((p-channel) or (padj channel)) and (p-channel) or (padj channel)) and (p-channel) or (padj channel)) and ((p-channel) or (padj channel)) and (p-channel) or (padj channel) angstroms) and ((p-channel) or (padj channel) angstroms) and ((p-channel) or (padj channel) angstroms) and (p-channel) or (padj channel) angstroms) and (p-channel) or (padj channel) angstroms) and (p-channel) or (padj channel) angstroms) and (p-channel or padj channel		ľ	(positiv\$3 same dop\$3))		
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cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (coxide adj layer) with ("50" adj angstroms)) and ((p adj channel) or (p-channel) and (floating adj layer) and (floating adj layer) and (floating adj gate) and (dielectric adj layer) and (floating adj layer) with ("50" adj angstroms)) and ((p-channel) or (p adj channel)) - 303 (memory adj cell) and (oxide adj layer) and (floating adj gate) and (ip-channel) or (p adj channel) o	_	0	438/264.762.763.ccls. and (memory adi		2003/11/13
			cell) and (oxide adj layer) and (floating	·	
with ("50" adj angstroms) and ((p adj channel) or (p-channel) ((memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (coxide adj layer) and (coxide adj layer) and (coxide adj layer) and (floating adj gate) and (dielectric adj layer) and (floating adj gate) and (dielectric adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((p-channel)) ((p-channel) or (p adj channel))					
18				DERWENT	
and (floating adj gate) and (diselectric adj layer) and (control adj gate) and (p-channel) or (p adj channel)) - 303 (memory adj cell) and (oxide adj layer) and (floating adj gate) and (diselectric adj layer) and (control adj gate) and (p-channel) or (p adj channel)) - 3 (memory adj cell) and (oxide adj layer) and (floating adj gate) and (diselectric adj layer) and (control adj gate) and (poxide adj layer) and (floating adj gate) and (diselectric adj layer) and (control adj gate) and (poxide adj layer) and (p-channel) or (p adj channel)) - 1 5 408115.pn. and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel)) - 13 (memory adj cell) and (oxide adj layer) band (floating adj gate) and (floating adj gate) and (floating adj gate) and ((oxide adj layer) band (oxide adj layer) band ((oxide adj layer) band (oxide adj layer) band (o					0002/11/05
adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms)) and ((p-channel) or (p adj channel))	-	. 18		·	• •
angstroms)) and ((p-channel) or (p adj channel)) (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (memory adj cell) and (oxide adj layer) DERWENT and (floating adj gate) and (dielectric adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (floating adj gate) and (floating adj gate) and (floating adj angstroms)) and ((p-channel) or (p adj channel)) 1 5408115.pn. and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel)) 1 (memory adj cell) and (oxide adj layer) with ("40" adj angstroms)) and (p-channel) or (p adj channel)) 1 (memory adj cell) and (oxide adj layer) with ((oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (floating adj angstroms)) and ((p-channel) or (p adj channel)) 1 (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (dielectric adj layer) and (control adj gate) and (dielectric adj layer) and (control adj gate) and (control			adj layer) and (control adj gate) and	EPO; JPO;	
Channel				DERWENT	
and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (control ad					
adj layer) and (control adj gate) and ((p-channel)) or (p adj channel)) DERWENT (SPAT; 2003/11/25 adj layer) and (floating adj gate) and (dielectric adj layer) and (p-channel) or (p adj channel)) S408115.pn. and ((p-channel) or (p adj channel)) S408115.pn. and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel)) S408115.pn. and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel)) S408115.pn. and ((oxide adj layer) with ("40" adj angstroms)) and (p-channel) or (p adj channel)) S408115.pn. and (footing adj gate) and (dielectric adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("30" adj angstroms)) and ((p-channel) or (p adj channel)) S408116.pn. and (floating adj gate) and (control adj gate) and ((oxide adj layer) with ("23" adj angstroms)) and ((p-channel) or (p adj channel) S408116.pn. and (p-channel) S408	-	303			' '
Cip-channel) or (p adj channel) DERWENT USPAT; 2003/11/25 2003					18:10
and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel)) - 1 5408115.pn. and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel)) - 13 (memory adj cell) and (oxide adj layer) and (floating adj gate) and ((oxide adj layer) and (floating adj gate) and ((oxide adj layer) and (control adj gate) and ((oxide adj layer) and (floating adj gate) and ((oxide adj layer) and (floating adj gate) and ((oxide adj layer) and (floating adj gate) and ((interpretation adj layer) and (p-channel)) - 13 (memory adj cell) and (oxide adj layer) and (floating adj gate) and ((oxide adj layer) and (floating adj gate) and ((oxide adj layer) and (p-channel)) - 13 (memory adj cell) and (oxide adj layer) and (floating adj gate) and ((interpretation)) and (interpretation) and (interpretation) and (p-channel) or (p adj channel)) - 14 (oxide adj layer) with ("23" adj angstroms)) and ((p-channel) or (p adj channel)) - 15 (afficial and (p-channel) or p adj channel) - 16 (afficial and (p-channel) or p adj channel) - 17 (afficial and (p-channel) or p adj channel) - 18 (afficial and (p-channel) or p adj channel) - 19 (afficial and (p-channel) or p adj channel) - 10 (afficial and (p-channel) or p adj channel) - 10 (afficial and (p-channel) or p adj channel) - 10 (afficial and (p-channel) or p adj channel) - 10 (afficial and (p-channel) or p adj channel) - 10 (afficial and (p-channel) or p adj channel) - 10 (afficial and (p-channel) or p adj channel) - 11 (afficial and (p-channel) or p adj channel) - 12 (afficial and (p-channel) or p adj channel) - 13 (afficial and (p-channel) or p adj channel) - 14 (afficial and (p-channel) or p adj channel) - 15 (afficial and (p-channel) or p adj channel) - 16 (afficial and (p-channel) or p adj channel) - 17 (afficial and (p-channel) or p adj channel) - 18 (afficial and (p-channel) or p adj channel) - 19 (afficial and (p-channel) or p adj channel) - 19 (affic			((p-channel) or (p adj channel))	DERWENT	
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- 13 (channel)) (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("23" adj angstroms)) and ((p-channel) or (p adj channel)) - 0 (6515328.pn. and (p-channel or p adj channel) - 0 (6372651.pn. and (p-channel or p adj channel) - 0 (6383939.pn. and (p-channel or p adj channel)			((oxide adj layer) with ("30" adj		
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- 0 6383939.pn. and (p-channel or p adj channel) - 0 6383939.pn. and (p-channel or p adj channel or p adj channel or p channel or p adj channel or p channel) DERWENT USPAT; 2003/11/26 14:04 USPAT; USPAT; 2003/11/26 USPAT; U				US-PGPUB;	
- 0 6383939.pn. and (p-channel or p adj channel) USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; channel or p adj channel or p channel) USPAT; US					
- 0 6383939.pn. and (p-channel or p adj channel or p channel) EPO; JPO; DERWENT USPAT; USPAT; US-PGPUB; L4:04 EPO; JPO;	-	0		USPAT;	
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-	0	438/257,263, 264,762,763.ccls. and	USPAT;	2004/04/17
1		(memory adj cell) and (oxide adj layer)	US-PGPUB;	14:35
1		and (floating adj gate) and (dielectric	EPO; JPO;	
Ì		adj layer) and (control adj gate) and	DERWENT	
		((oxide adj layer) with ("40" adj		
		angstroms))		
-	0	438/257,263, 264,762,763.ccls. and	USPAT;	2003/11/29
		(memory adj cell) and (oxide adj layer)	US-PGPUB;	16:05
		and (floating adj gate) and (dielectric	EPO; JPO;	
		adj layer) and (control adj gate) and	DERWENT	1
		(oxide adj layer)		
-	0	438/257,263, 264,762,763.ccls. and	USPAT;	2004/04/17
		(memory adj cell) and (oxide adj layer)	US-PGPUB;	14:33
		and (floating adj gate) and (dielectric	EPO; JPO;	
		adj layer) and (control adj gate)	DERWENT	